

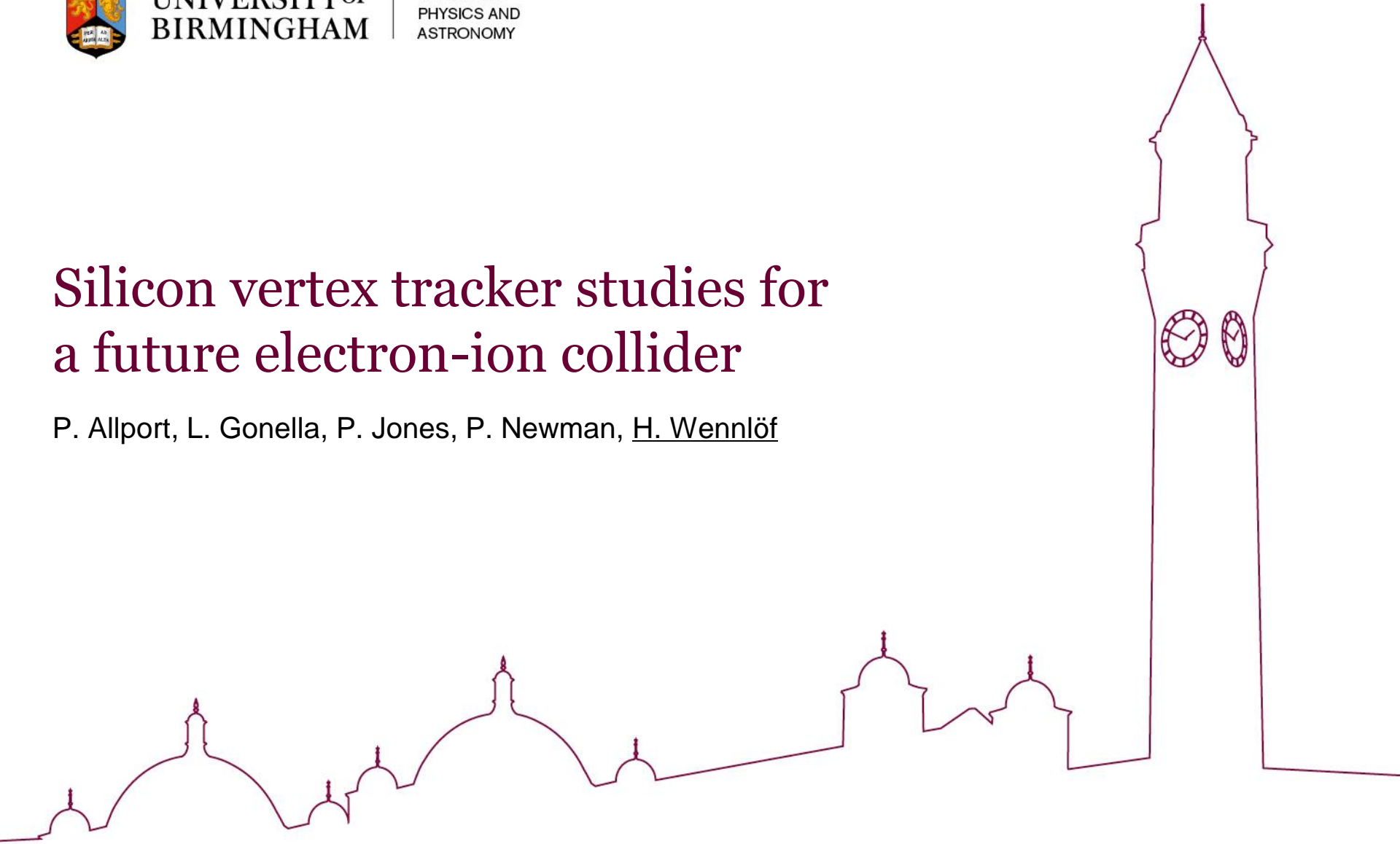


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Silicon vertex tracker studies for a future electron-ion collider

P. Allport, L. Gonella, P. Jones, P. Newman, [H. Wennl6f](#)



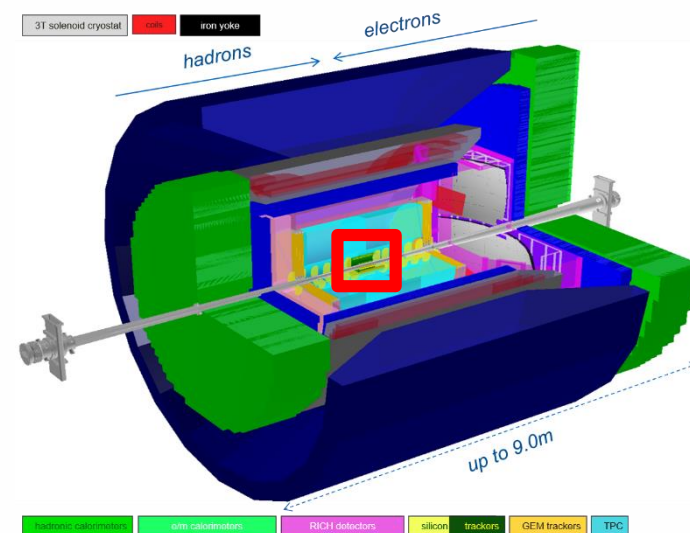
Outline

- Silicon vertex tracker
 - Why is it important?
- Simulations
 - Geometric parameters of the SVT
- Pixel sensors
 - The parts that make up the SVT
- Towards an EIC-specific sensor
- Conclusions and outlook



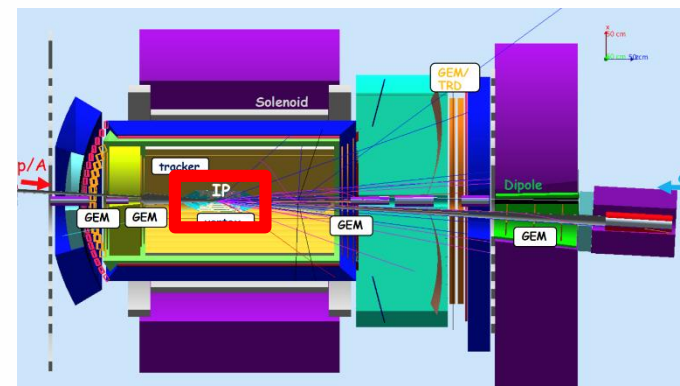
Silicon vertex tracker

- Innermost part of the detector.
- Main detector for **vertex position finding**
- Contributes to **momentum measurements**
- Requires:
 - **Very fine spatial resolution**, to separate primary and secondary vertices
 - **Low material**, to reduce multiple scattering
- Baseline used in studies: ALICE ITS upgrade



BeAST concept (BNL)

<https://indico.cern.ch/event/722363/contributions/3031250/>



JLEIC concept (JLab)

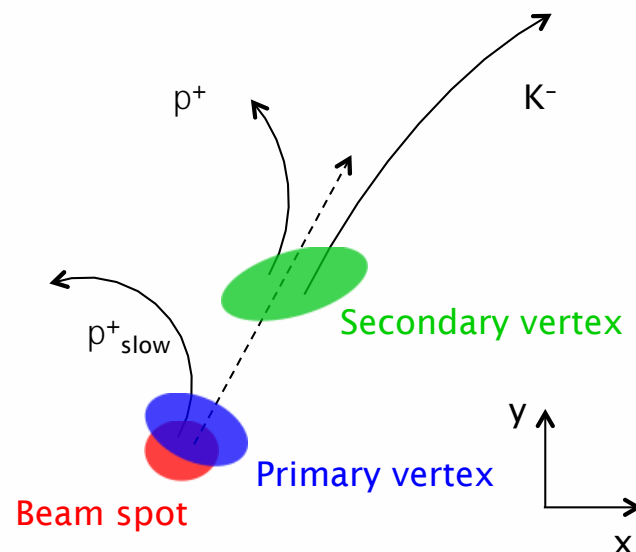
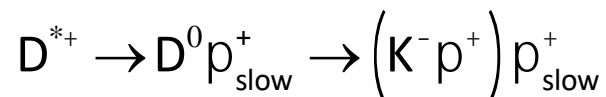
<http://accelconf.web.cern.ch/AccelConf/ipac2017/papers/thpab084.pdf>

Open charm reconstruction

- Signature is **displaced (secondary) decay vertex**

| Particle | Decay | Branching | $c\tau$ [μm] |
|----------|--------------------------|-----------|---------------------------|
| D^0 | $K^-\pi^+$ | 3.9% | 123 |
| D^+ | $K^-\pi^+\pi^+$ | 9.5% | 311 |
| D^{*+} | $D^0\pi^+_{\text{slow}}$ | 67.7% | |

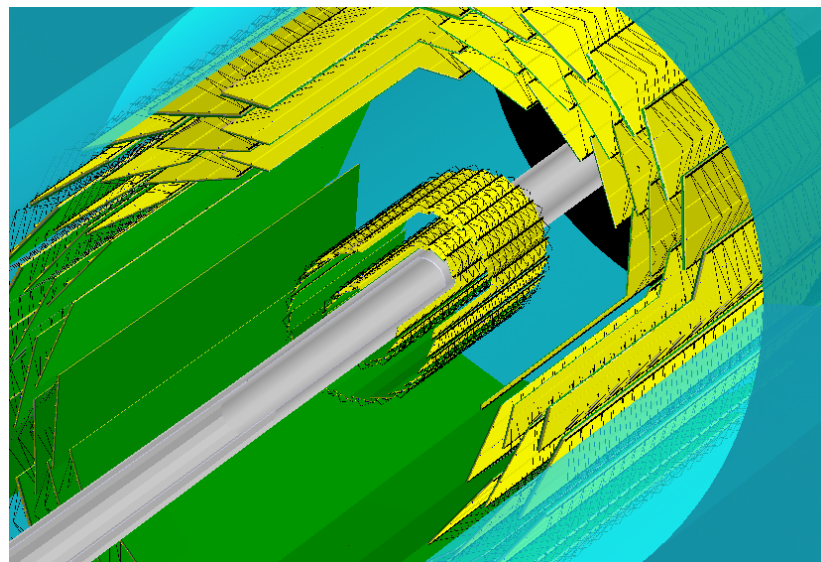
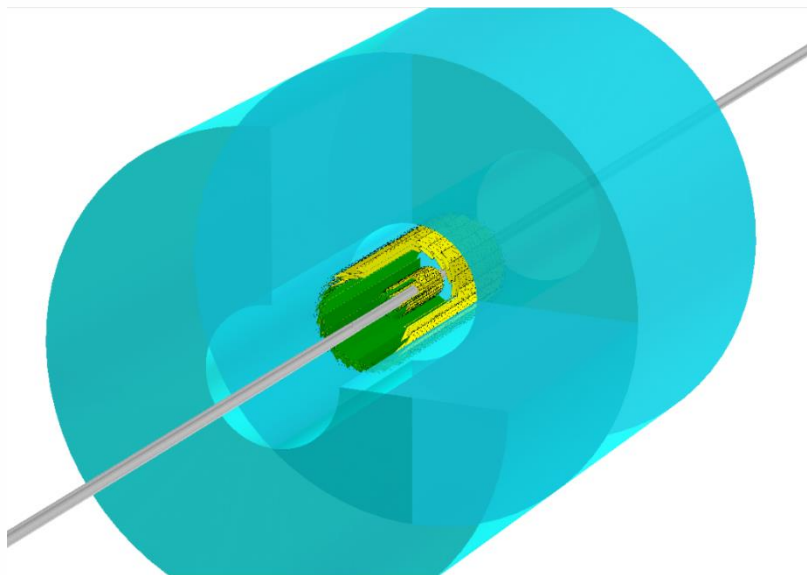
Example:



- Requires excellent impact parameter resolution in r - ϕ and z
 - Dominated by **position** and **resolution** of innermost tracking layer
 - Close as possible to beam pipe
 - Highest possible spatial resolution

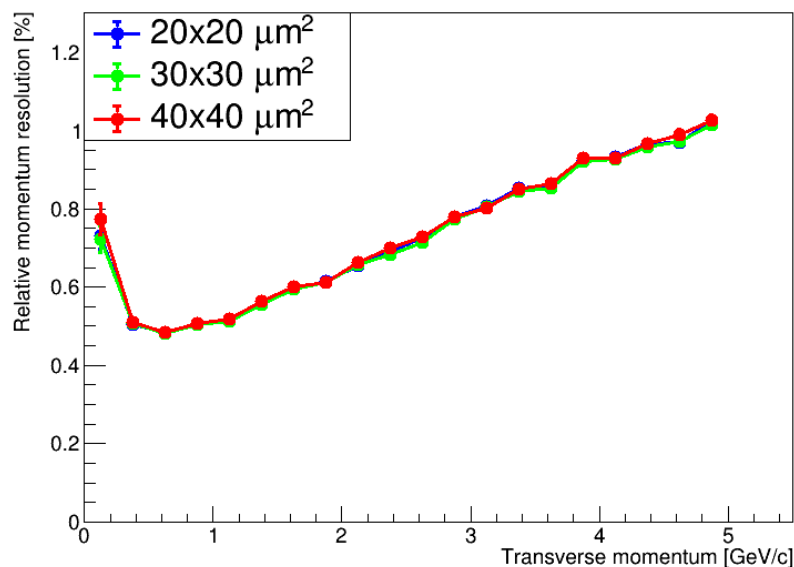
Simulation studies

- Studies of full silicon vertex tracker done using **EICROOT**
 - A specific simulation package for the EIC, containing particle generator, GEANT propagation, hit digitisation, and track finding
- **Momentum resolution** and **pointing resolution** studied
- Different layouts and pixel sizes investigated

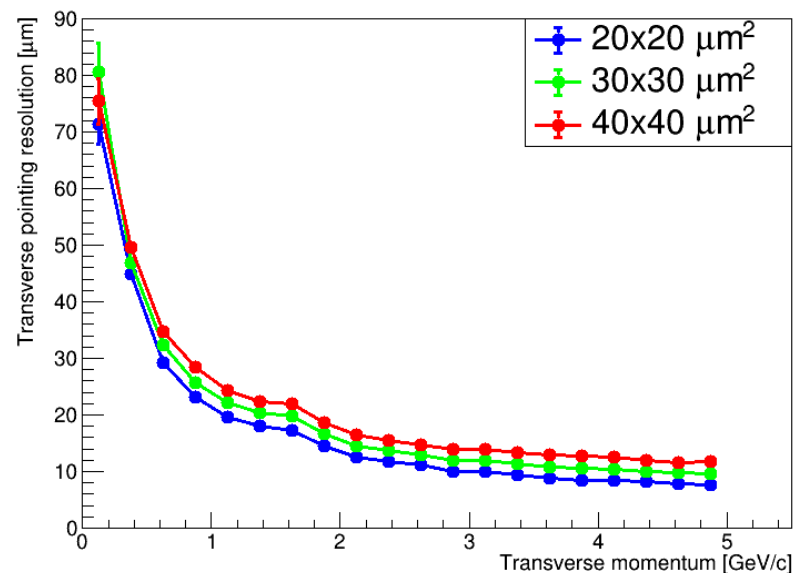


Simulation results – barrel pixel size

Relative momentum resolution



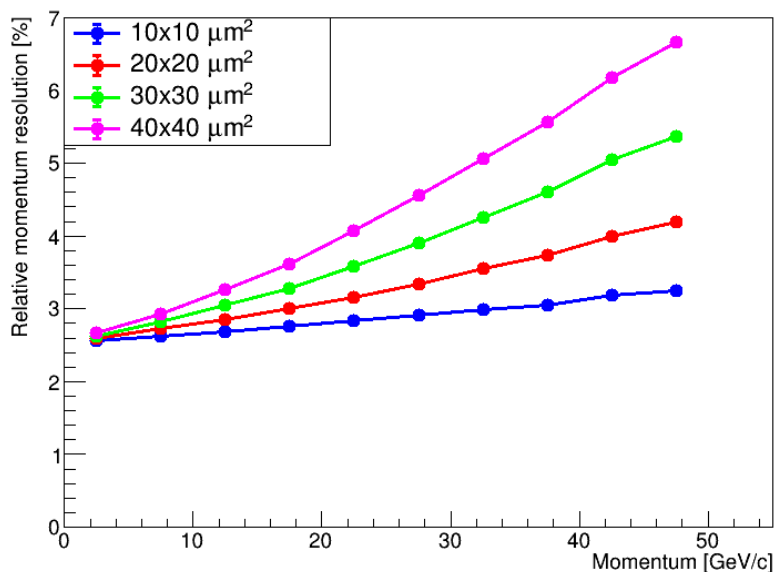
Transverse pointing resolution



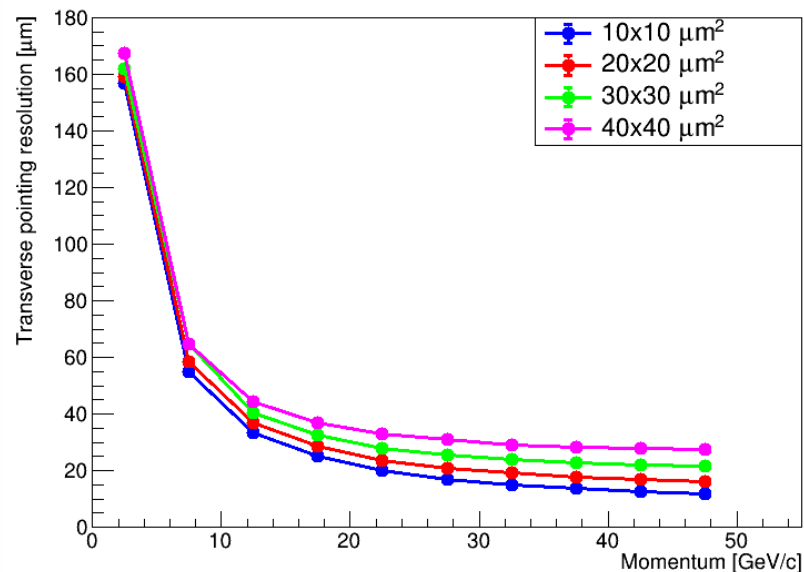
- Pseudorapidity $|\eta| < 0.5$ (barrel region)
- Pixel size has no effect on momentum resolution
- Pointing resolution improves with reduced pixel size

Simulation results – disk pixel size

Relative momentum resolution



Transverse pointing resolution

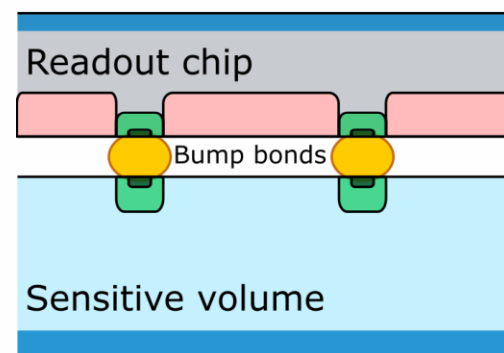


- Pseudorapidity $\eta = 3$ (disk region)
- Both **momentum resolution** and **pointing resolution** improve with reduced pixel size
- For best performance: **use small pixels** located **near the interaction point**

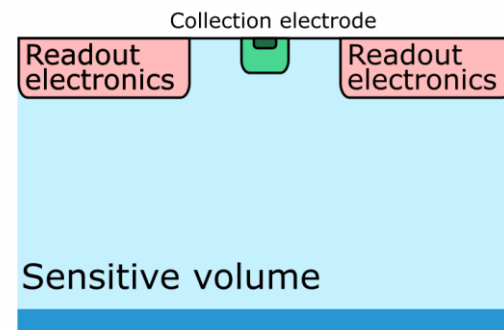
Pixel sensors

- Hybrids
 - Sensitive volume and readout electronics on separate chips
 - Up until now most commonly used in silicon vertex trackers
 - Radiation tolerant and fast
- Monolithic Active Pixel Sensors (MAPS)
 - Sensitive volume and readout electronics on same chip
 - Made using commercial CMOS technology
 - Thin and fine granularity
- Depleted Monolithic Active Pixel Sensors (DMAPS)
 - Utilising high voltage/high resistivity CMOS technology
 - Depleted volume intended to be as large as possible

Hybrid sensor

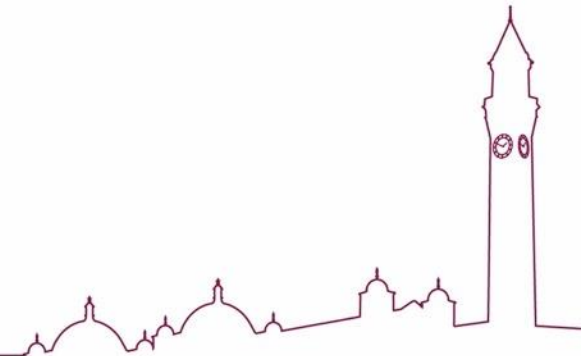


Monolithic sensor



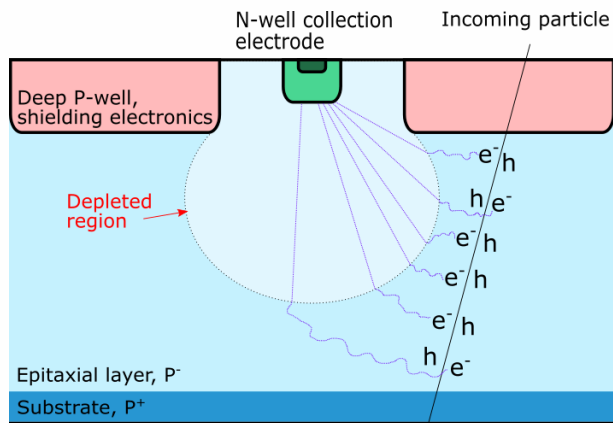
Advantages of DMAPS

- Lower cost
 - Mass production in commercial CMOS technologies
 - Lower material budget
 - Avoids bump-bonding (complex and laborious)
-
- Depletion gives **faster** and **more uniform** charge collection compared to standard MAPS

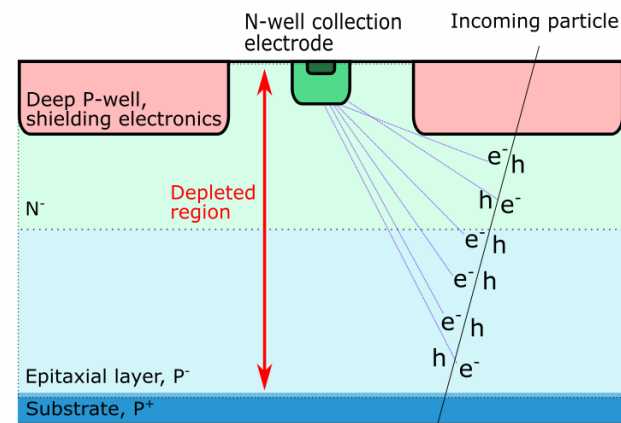


TowerJazz Investigator

- TowerJazz 180 nm CMOS imaging process
- Monolithic test chip, with many different pixel flavours.
 - Different pixel size, collection electrode size, spacing between collection electrode and p-well with electronics
- Two process versions; standard and modified
 - Modified has a deep planar junction to **increase depletion**
- Measurements made using iron-55 source.



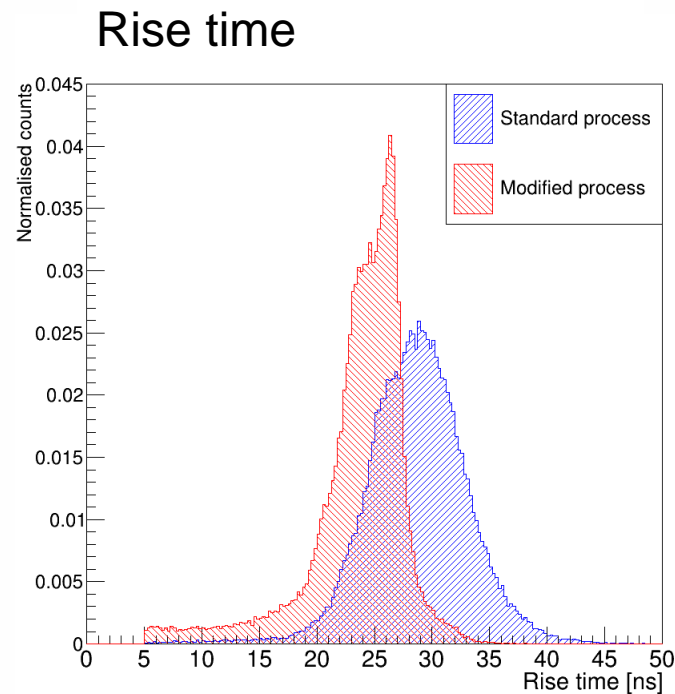
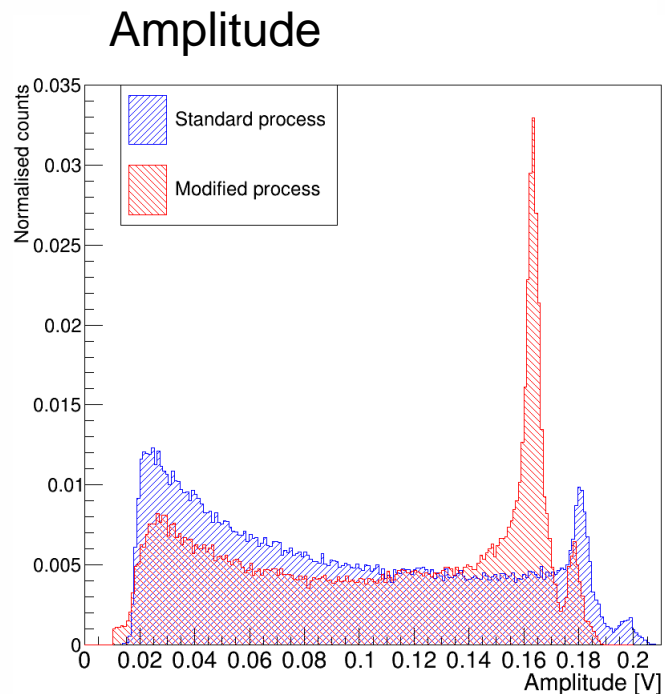
Standard process (MAPS)



Modified process (DMAPS)

Results

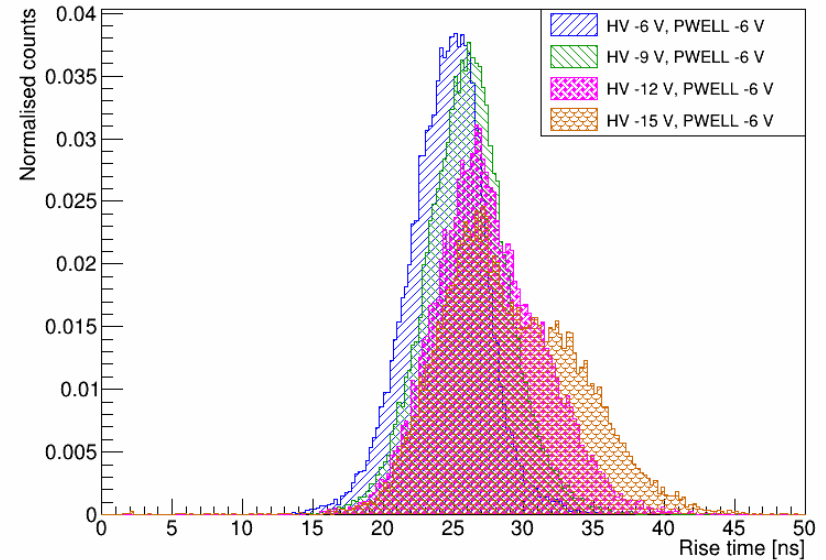
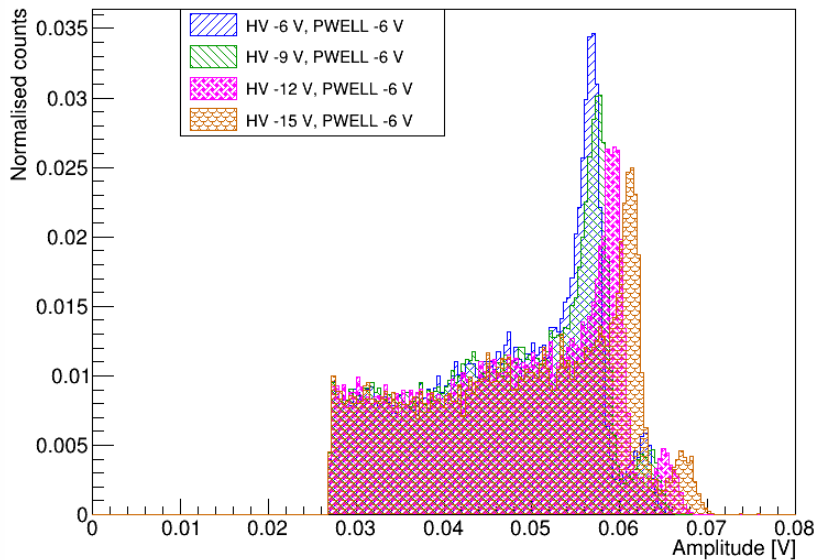
- Results shown for a $28 \times 28 \mu\text{m}^2$ pixel



- For a $20 \times 20 \mu\text{m}^2$ pixel, the differences are smaller
- For larger pixels and spacing, the modified process shows worse performance

Results

- Chip in modified process dubbed TJ1B enables separate biasing of p-well and substrate (HV)
- Results of different substrate biasing shown below

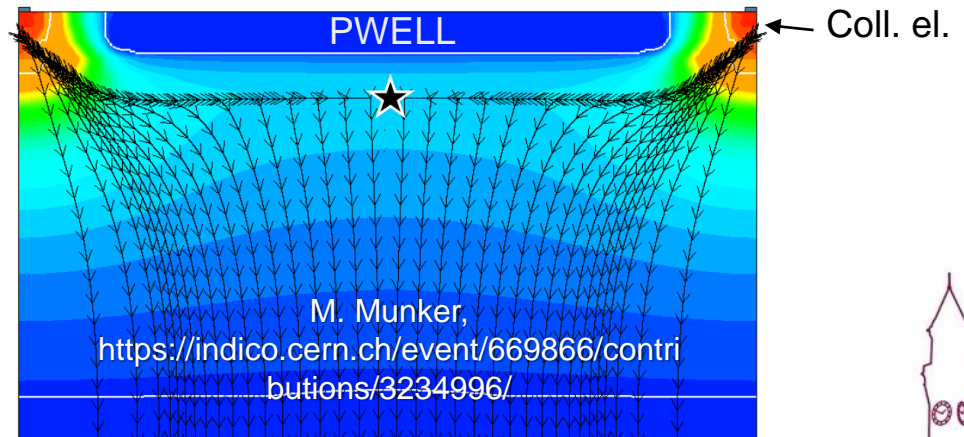


- Increasing substrate voltage **decreases signal-to-noise ratio**
- Increasing substrate voltage makes rise-time distribution **wider**

Conclusions of technology investigation

- Modified process performs better up to $30 \times 30 \mu\text{m}^2$ pixel size
- Smaller difference between processes at smaller pixels
 - Due to higher relative depletion already in the standard process
- Higher bias voltage does **not** improve signal
 - Due to shape of electric field: **minimum at pixel border**
- Results consistent with simulations and published results from similar sensor [1]
- Higher potential difference between p-well and substrate gives **longer path** and **slower charge collection**

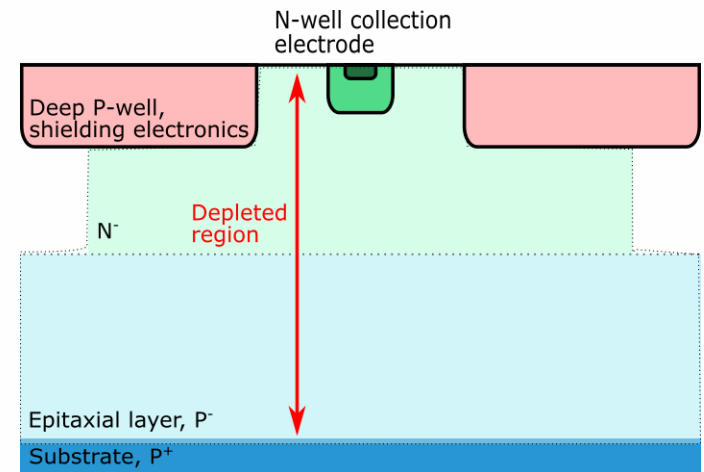
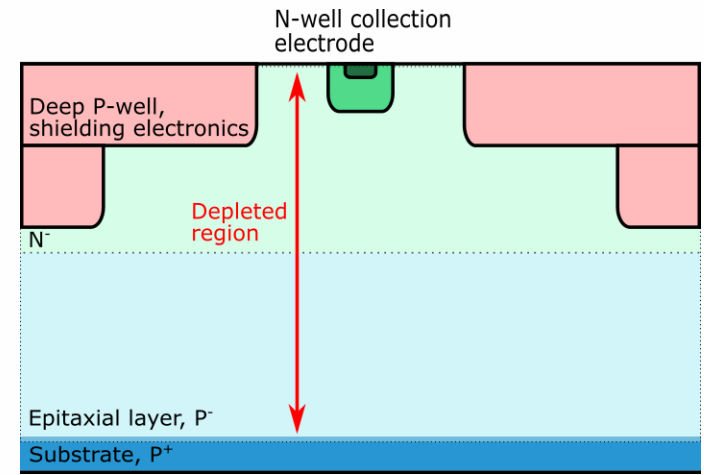
TCAD simulation - electrostatic potential minimum at pixel border:



[1] M. Munker et al. <https://doi.org/10.1088/1748-0221/14/05/C05013>

miniMALTA chip

- Pixels modified to fix the problem at edges
 - Extra deep p-well
 - Gap in the n layer
- Both modifications made to "funnel" the electric field towards collection electrode
- Analysis ongoing of testbeams of this chip. Initial results positive
- Publication in the works



M. Munker et al.
<https://doi.org/10.1088/1748-0221/14/05/C05013>

Towards an EIC-specific sensor

- Work with chip designers at the Rutherford Appleton Laboratory (RAL)
- Goals:
 - Develop high-granularity silicon vertex tracker
 - Investigate feasibility of time-stamping layer
- Time-stamping bunch crossings keeps track of **polarisation** in event
- Challenges: timing and pixel size
- Latest results: Timing resolution of **4 ns** can be reached, using a constant fraction discriminator
 - **Not possible in small pixels**
- Study ongoing

| | EIC DMAPS Sensor | |
|---|--|-------------------------------|
| Detector | Silicon vertex tracker | Time stamping layer |
| Technology | TowerJazz 180 nm | |
| Pixel size [$\mu\text{m} \times \mu\text{m}$] | 20x20 | Max 350x350 |
| Integration time | 2000 ns | |
| Timing resolution | N/A | < 9 ns (BNL) < 1 ns (JLAB) |
| Power | < 35 mW/cm ² | |
| Radiation fluence | < 10 ¹⁰ 1 MeV neq/cm ² | |

Conclusions and outlook

- Results so far:
 - Simulations show that we want **small pixel size** and detector layers **close to the beampipe**
 - TowerJazz modified process suits our needs, but **sensor layout is crucial**
 - Extra modifications can potentially be beneficial
 - Needs further investigation
- Current work:
 - Analysing miniMALTA testbeam data
 - Finish simulating different detector layouts, focusing on the area encompassing both barrel and disks
- Future work:
 - Continued sensor development with RAL
 - Full event reconstruction in simulations, investigating heavy-flavour observables
 - Test of single-photon avalanche diodes (SPADs)
 - Tests of the TowerJazz MonoPix chip (from Bonn)



Thank you for your attention



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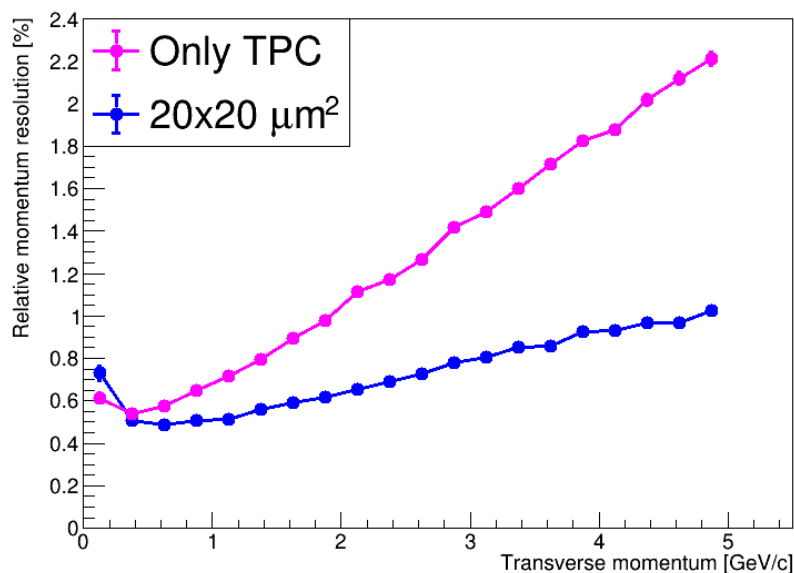
BILPA

EIC R&D
eRD18

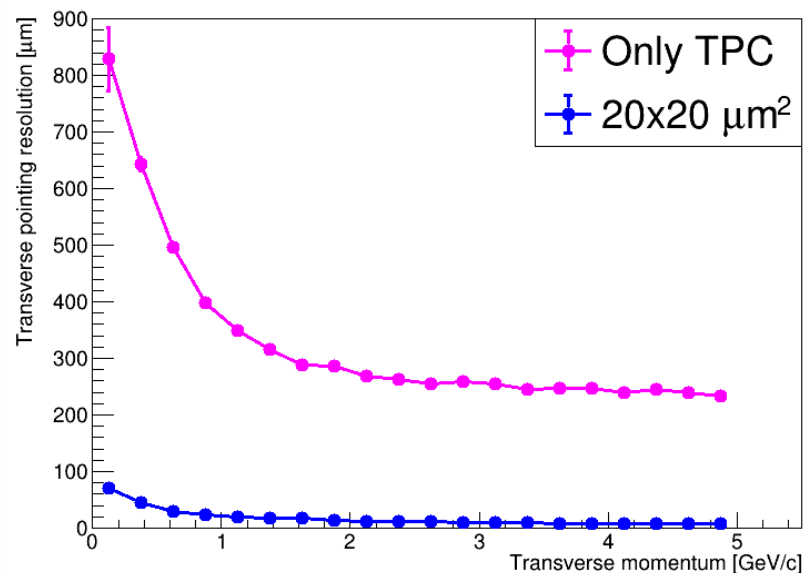
Backup

Simulation results

Relative momentum resolution



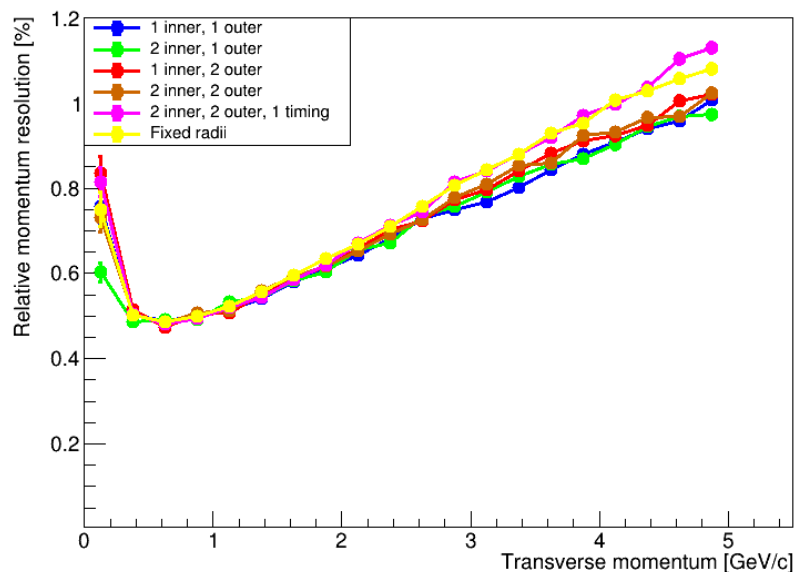
Transverse pointing resolution



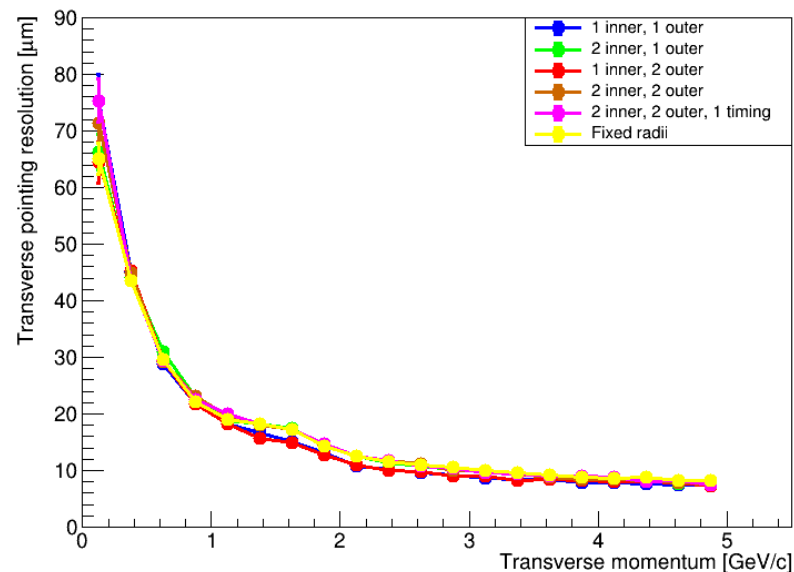
- Relative momentum resolution better for only TPC at very low momenta, due to multiple scattering
- Everywhere else, a SVT improves performance

Simulations – different layouts

Relative momentum resolution



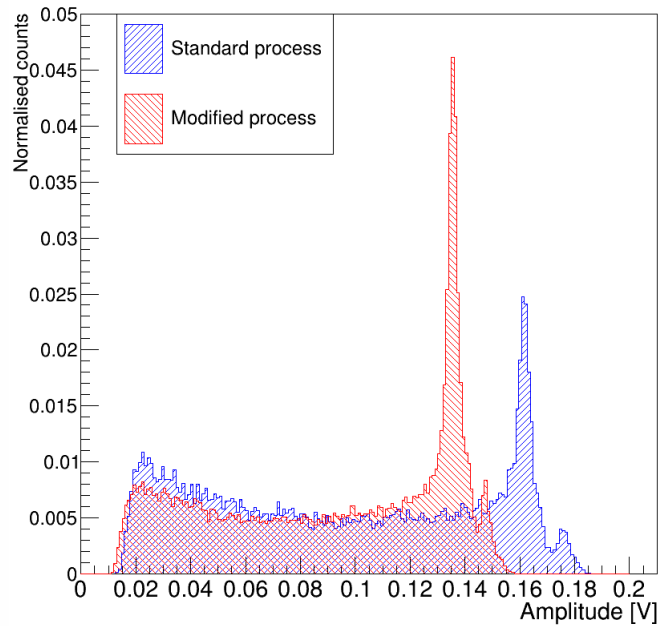
Transverse pointing resolution



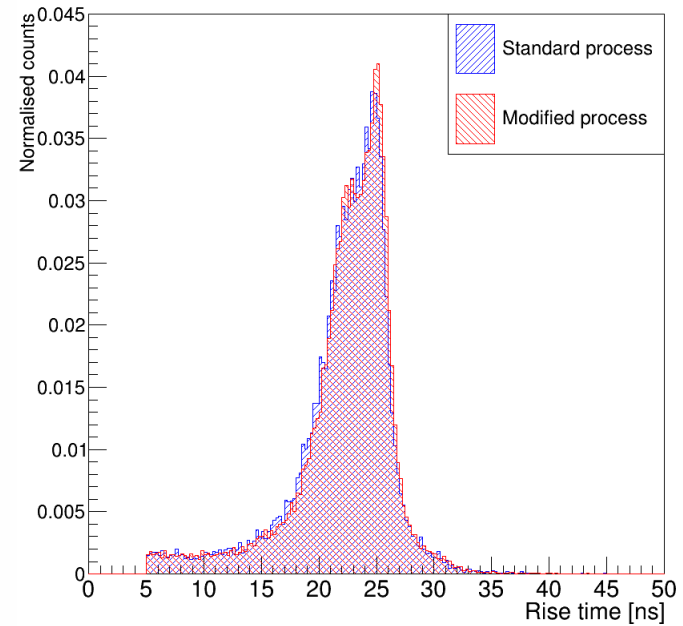
- Different layer configurations and positions (details available on request)
- Not much difference for different configurations
- relative momentum resolution slightly worse when a thick timing layer (1.6% X_0) is added
 - This is the case in "fixed radii" as well

Results - 20x20 μm^2 pixel

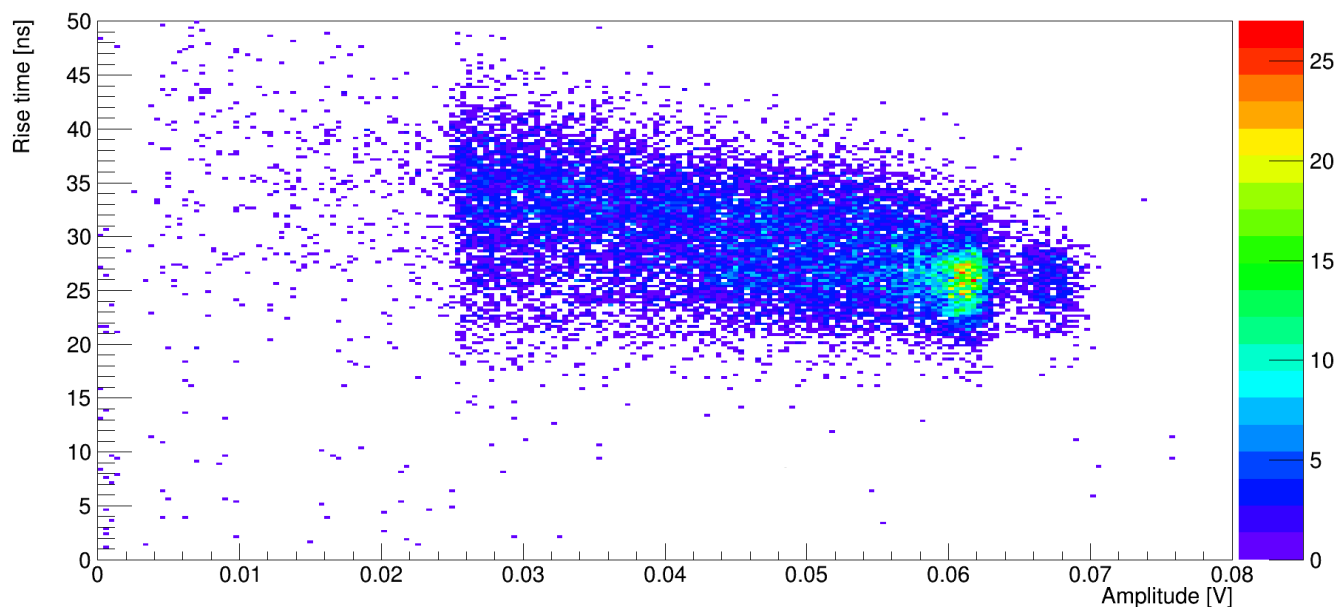
Matrix 02



Matrix 02



Rise time vs amplitude



- 28x28 μm^2 pixel, HV -15 V, PWELL -6 V
- Smaller charges come from pixel border (due to charge sharing)
- Smaller charges have longer rise times
- Conclusion: Increasing HV makes charges from pixel edges arrive later at the collection electrode